

SN65MLVD048 四通道 M-LVDS 接收器

1 特性

- 低电压差分 30Ω 至 55Ω 线路接收器，信号传输速率¹高达 250Mbps；时钟频率高达 125MHz
- 1 类接收器具有 25mV 输入阈值迟滞
- 2 类接收器提供 100mV 偏移阈值，可检测开路和空闲总线状态
- 宽接收器输入共模电压范围为 -1V 至 3.4V，允许 2V 接地噪声
- 多点拓扑符合或超过 M-LVDS 标准 TIA/EIA-899
- $V_{CC} \leq 1.5V$ 时具有高输入阻抗
- 增强型 ESD 保护：针对所有引脚的 7kV HBM
- 48 引脚 7 X 7 QFN (RGZ)

2 应用

- 通过背板和电缆进行并行多点数据和时钟传输
- 蜂窝基站
- 局端交换机
- 网络交换机和路由器

3 说明

SN65MLVD048 是一款四通道 M-LVDS 接收器。该器件的设计完全符合 TIA/EIA-899 (M-LVDS) 标准，设计经过优化，可在高达 250Mbps 的信号传输速率下运行。每个接收器通道都由一个接收使能 ($\overline{RE}$) 控制。当 $\overline{RE}$ = 低电平时，对应的通道被启用；当 $\overline{RE}$ = 高电平时，对应的通道被禁用。

M-LVDS 标准定义了两种接收器类型，即 1 类和 2 类。1 类接收器的阈值以零为中心，迟滞为 25mV，可防止输入丢失时出现输出振荡；2 类接收器使用偏移阈值实现失效防护。对接收器输出端进行压摆率控制以减少与大电流浪涌相关的 EMI 和串扰影响。

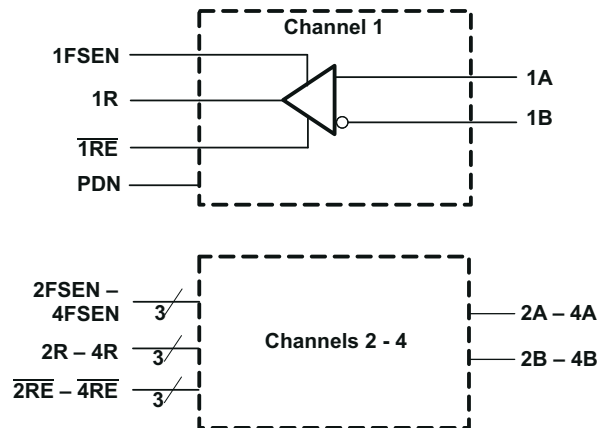
这些器件的额定工作温度范围为 -40°C 至 85°C。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 ⁽²⁾
SN65MLVD048	VQFN (RGZ, 48)	7mm x 7mm

(1) 如需了解更多信息，请参阅 节 10。

(2) 封装尺寸 (长 × 宽) 为标称值，并包括引脚 (如适用)。



逻辑图 (正逻辑)

¹ 线路的信号传输速率是指每秒钟的电压转换次数，单位为 bps (每秒比特数)。



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4 Pin Configuration and Functions

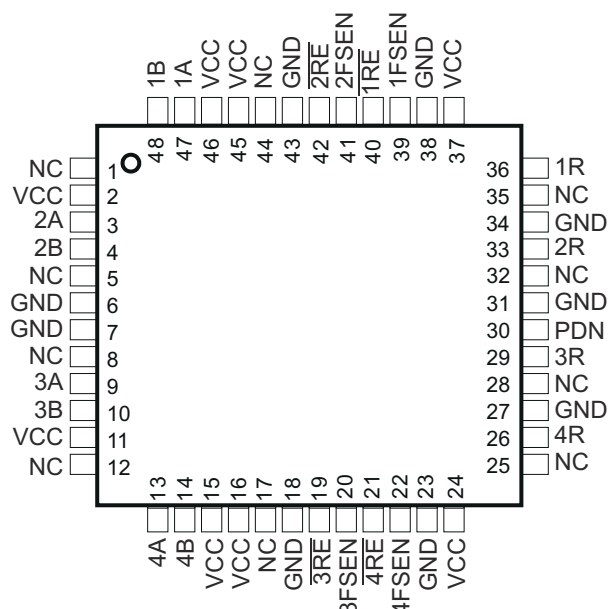


图 4-1. RGZ Package (Top View)

PIN		I/ O ⁽¹⁾	DESCRIPTION
NAME	NO.		
1R - 4R	36, 33, 29, 26	O	Data output from receivers
1A - 4A	47, 3, 9, 13	I/O	M-LVDS bus non-inverting input/output
1B - 4B	48, 4, 10, 14	I/O	M-LVDS bus inverting input/output
GND	6, 7, 18, 23, 27, 31, 34, 38, 43	I	Circuit ground. ALL GND pins must be connected to ground.
V _{CC}	2, 11, 15, 16, 24, 37, 45, 46	I	Supply voltage. ALL VCC pins must be connected to supply.
$\overline{1RE}$ - $\overline{4RE}$	40, 42, 19, 21	I	Receiver enable, active low, enables individual receivers. When this pin is left floating, internally this pin will be pulled to logic HIGH.
1FSEN - 4FSEN	39, 41, 20, 22	I	Failsafe enable pin. When this pin is left floating, internally this pin will be pulled to logic HIGH. This pin enables the Type 2 receiver for the respective channel. xFSEN = L → Type 1 receiver inputs xFSEN = H → Type 2 receiver inputs
PDN	30		Power Down pin. When this pin is left floating, internally this pin will be pulled to logic LOW. When PDN is HIGH, the device is powered up. When PDN is LOW, the device overrides all other control and powers down. All outputs are Hi-Z
NC	1, 5, 8, 12, 17, 25, 28, 32, 35		Not Connected
NC	44		Not Connected. Internal TI Test pin. This pin must be left unconnected.
PowerPAD™	-		Connected to GND

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	TYP	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾	– 0.5		4	V
	Input voltage range	RE, FSEN		4	V
		A or B		4	V
	Output voltage range	R		4	V
P _D	RE at 0V, C _L = 15pF, V _{ID} = 400mV, 125MHz			339	mW
T _{stg}	Storage Temperature	– 65		150	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±7000
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1500

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	3	3.3	3.6	V
V _{IH}	High-level input voltage	2		V _{CC}	V
V _{IL}	Low-level input voltage	GND		0.8	V
V _A or V _B	Voltage at any bus terminal	– 1.4		3.8	V
V _{ID}	Magnitude of differential input voltage	0.05		V _{CC}	V
V _{IC}	Differential common-mode input voltage	– 1		3.4	V
R _L	Differential load resistance	30	50		Ω
1/t _{UI}	Signaling rate			250	Mbps
T _A	Operating free-air temperature	– 40		85	°C

5.4 Package Dissipation Ratings

PACKAGE ⁽¹⁾	PCB TYPE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ⁽²⁾ ABOVE T _A = 25°C	T _A = 85°C POWER RATING
48-Pin QFN (RGZ)	Low-K	1298 mW	12.98 mW/°C	519 mW
	High-K	3448 mW	34.48 mW/°C	1379 mW

- (1) The thermal dissipations are in the consideration of soldering down the powerPAD without via on each type of boards.
- (2) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

5.5 Thermal Information

THERMAL METRIC ⁽¹⁾		RGZ	UNIT
		48-Pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	25.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	15.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	8.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	8.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.4	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

5.6 Device Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC}	Supply current	$\overline{RE}$ at 0V for all channels $C_L = 15\text{pF}$, $V_{ID} = 400\text{mV}$, 125MHz		86	94	mA
	Power down	PDN = L		0.75	1.5	mA

(1) All typical values are at 25°C and with a 3.3V supply voltage.

5.7 Receiver Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IT+}	Positive-going differential input voltage threshold	Type 1	See 表 6-1 and 表 6-2			35	mV
		Type 2				135	
V _{IT-}	Negative-going differential input voltage threshold	Type 1		- 35		65	mV
		Type 2					
V _{HYS}	Differential input voltage hysteresis (V _{IT+} - V _{IT-})	Type 1		25		0	mV
		Type 2					
V _{OH}	High-level output voltage	I _{OH} = - 8mA		2.4		V	
V _{OL}	Low-level output voltage	I _{OL} = 8mA		0.4		V	
I _{IH}	High-level input current	V _{IH} = 2V to V _{CC}		- 10		μ A	
I _{IL}	Low-level input current	V _{IL} = GND to 0.8V		- 10		μ A	
I _{OZ}	High-impedance output current	V _O = 0V or V _{CC}		- 10		15 μ A	
I _A or I _B	Receiver input current	One input (V _A or V _B) = - 1.4V or 3.8V, Other input = 1.2V		- 20		20 μ A	
I _{AB}	Receiver differential input current (I _A - I _B)	V _A = V _B = - 1.4V or 3.8V		- 4		4 μ A	
I _{A(OFF)} or I _{B(OFF)}	Receiver input current	One input (V _A or V _B) = - 1.4V or 3.8V, Other input = 1.2V, V _{CC} = GND or 1.5V		- 32		32 μ A	
I _{AB(OFF)}	Receiver power-off differential input current (I _A - I _B)	V _A = V _B = - 1.4V or 3.8V, V _{CC} = GND or 1.5V		- 4		4 μ A	
C _A or C _B	Input capacitance	V _I = 0.4sin(30E6 π t) + 0.5V, ⁽²⁾ Other input at 1.2V		5		pF	
C _{AB}	Differential input capacitance	V _{AB} = 0.4sin(30E6 π t) + 0.5V ⁽²⁾		3		pF	
C _{A/B}	Input capacitance balance, (C _A /C _B)			0.99		1.01	

(1) All typical values are at 25°C and with a 3.3V supply voltage.

(2) HP4194A impedance analyzer (or equivalent)

5.8 Receiver Switching Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		C _L = 15pF, See 图 6-2		2		6	ns
t _{PHL}	Propagation delay time, high-to-low-level output				2		6	ns
t _r	Output signal rise time				1		2.3	
t _f	Output signal fall time				1		2.3	ns
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	Type 1				35	270	ps
		Type 2				150	460	
t _{sk(pp)}	Part-to-part skew						800	ps
t _{jit(per)}	Period jitter, rms (1 standard deviation) ⁽²⁾		All channels switching, 125MHz clock input ⁽³⁾ , See 图 6-4			6	ps	
t _{jit(c-c)}	Cycle-to-cycle jitter, rms ⁽²⁾					13	ps	
t _{jit(det)}	Deterministic jitter ⁽²⁾	Type 1	All channels switching, 250Mbps 2 ¹⁵ -1 PRBS input ⁽³⁾ , See 图 6-4			800	ps	
		Type 2				945	ps	
t _{jit(ran)}	Random jitter ⁽²⁾	Type 1				9	ps	
		Type 2				8	ps	
t _{PZH}	Enable time, high-impedance-to-high-level output		C _L = 15pF, See 图 6-3			15	ns	
t _{PZL}	Enable time, high-impedance-to-low-level output		C _L = 15pF, See 图 6-3			15	ns	
t _{PHZ}	Disable time, high-level-to-high-impedance output		C _L = 15pF, See 图 6-3			10	ns	
t _{PLZ}	Disable time, low-level-to-high-impedance output		C _L = 15pF, See 图 6-3			10	ns	

(1) All typical values are at 25°C and with a 3.3V supply voltage.

(2) Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.

(3) $t_r = t_f = 0.5\text{ns}$ (10% to 90%)

5.9 Typical Characteristics

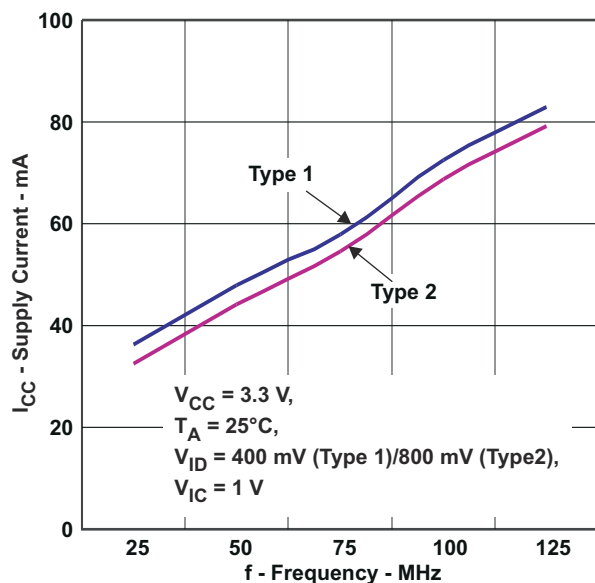


图 5-1. Supply Current vs Frequency

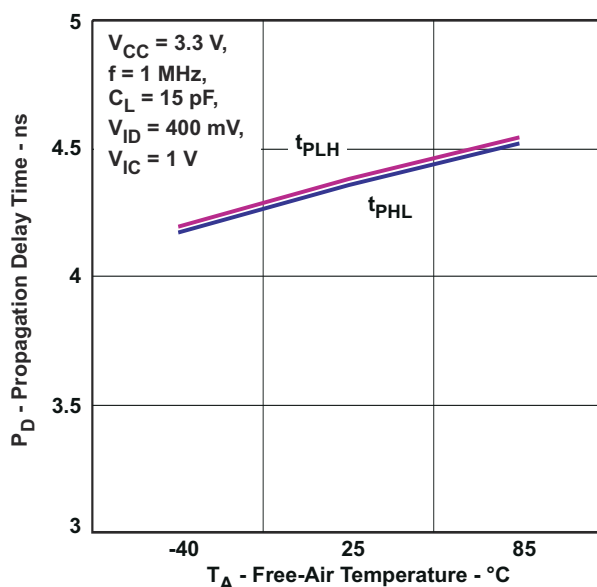


图 5-2. Receiver (Type-1) Propagation Delay Time vs Free-Air Temperature

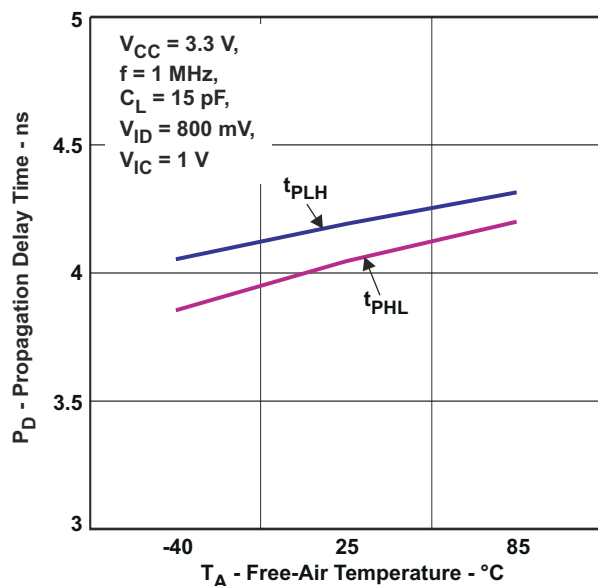


图 5-3. Receiver (Type-2) Propagation Delay Time vs Free-Air Temperature

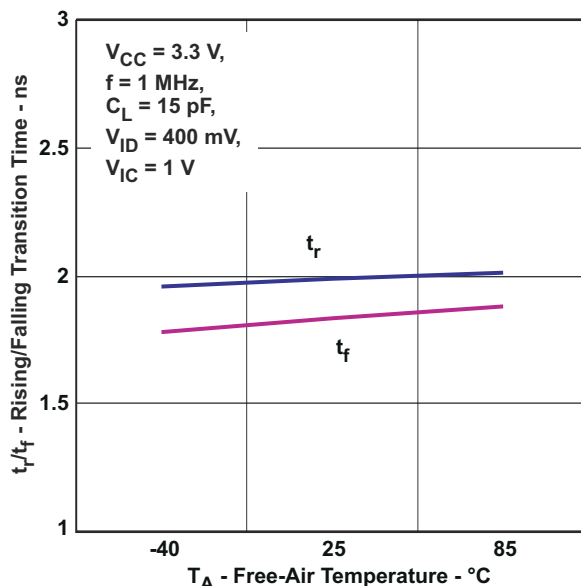


图 5-4. Receiver (Type-1) Transition Time vs Free-Air Temperature

5.9 Typical Characteristics (continued)

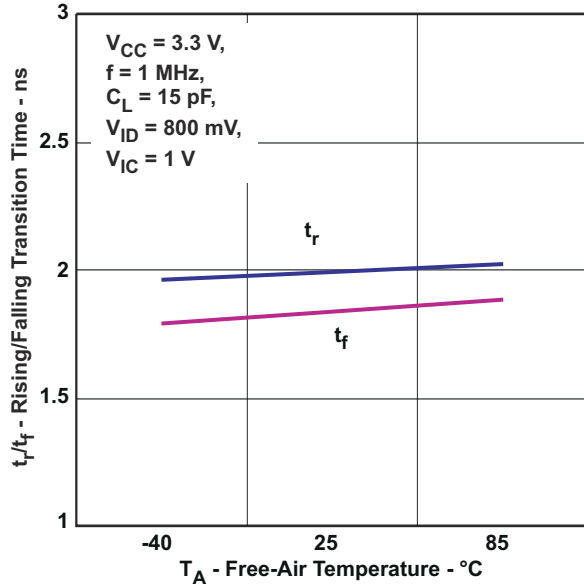


图 5-5. Receiver (Type-2) Transition Time vs Free-Air Temperature

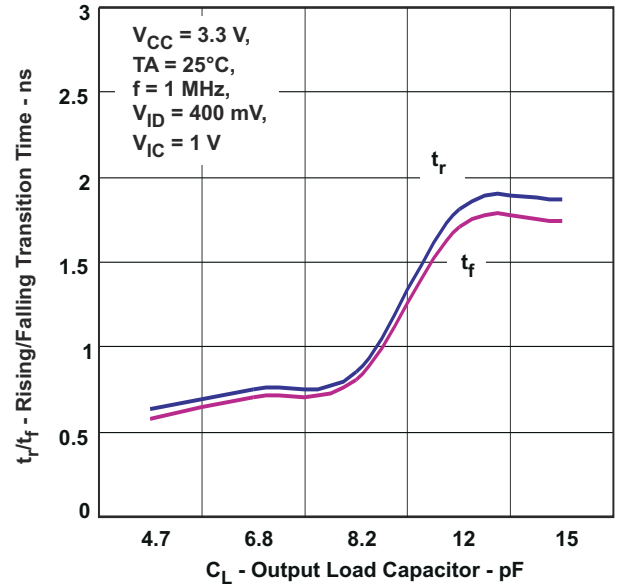


图 5-6. Receiver (Type-1) Transition Time vs Output Load Capacitor

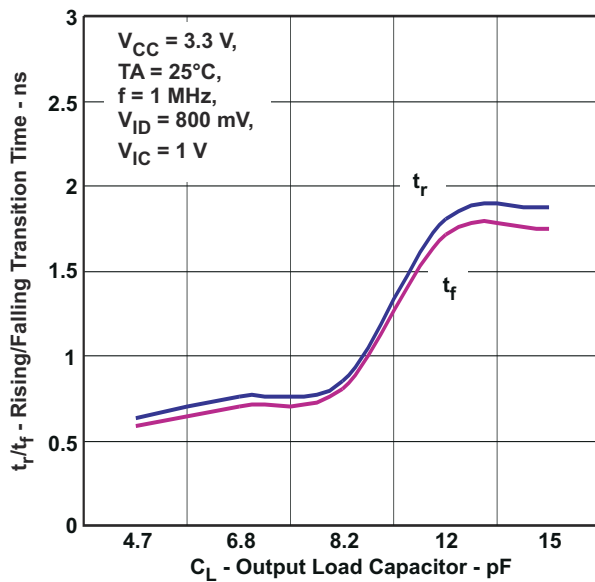


图 5-7. Receiver (Type-2) Transition Time vs Output Load Capacitor

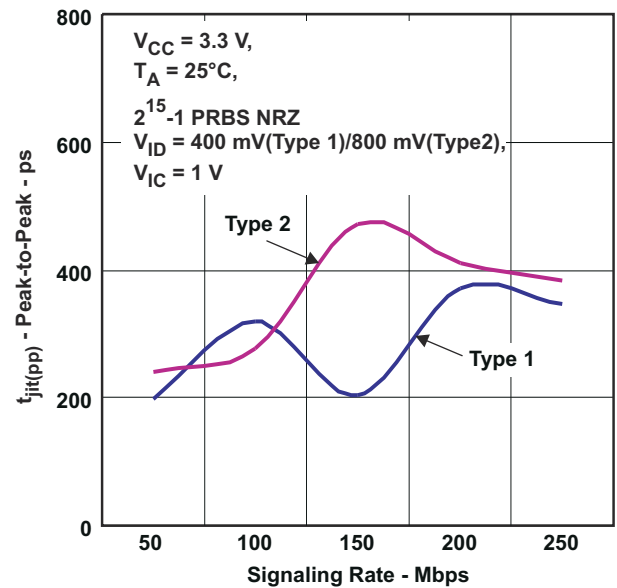


图 5-8. Added Receiver Peak-to-Peak Jitter vs Signaling Rate

5.9 Typical Characteristics (continued)

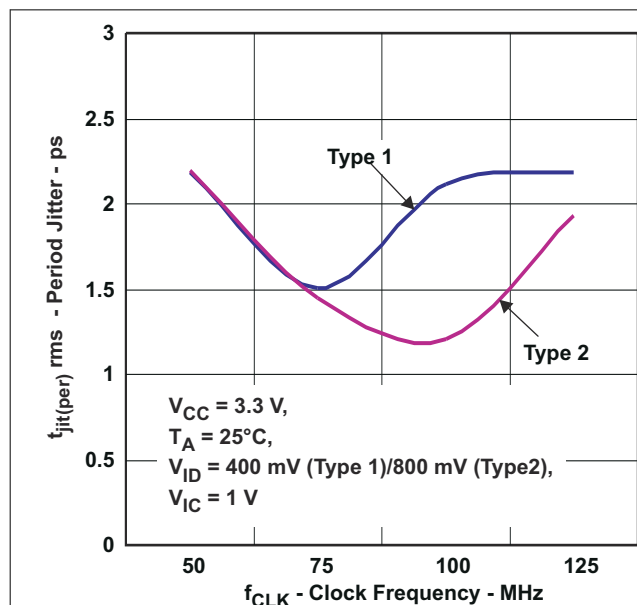


图 5-9. Added Receiver Period Jitter vs Clock Frequency

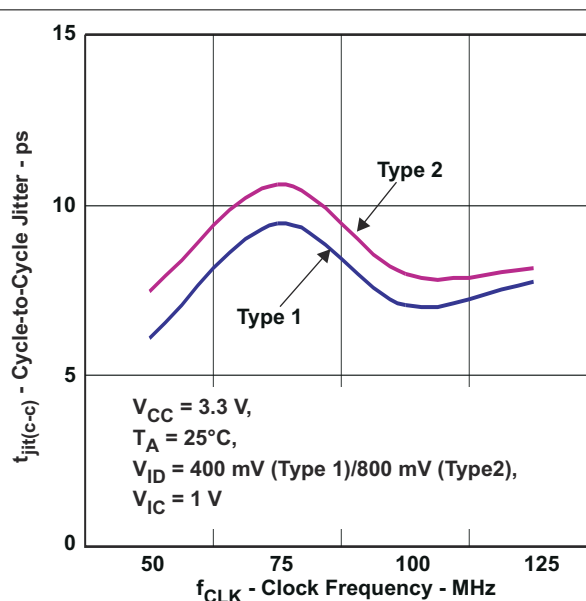
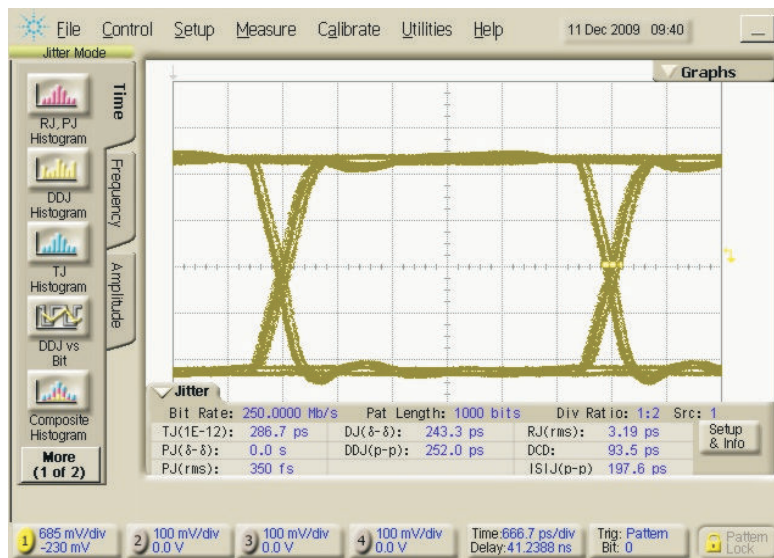


图 5-10. Added Receiver Cycle-to-Cycle Jitter vs Clock Frequency

5.9.1 Eye Patterns

图 5-11. Output ($V_{CC} = 3.3V$, $V_{ID} = 400mV$) 250Mbps $2^{15} - 1$ PRBS, Receiver Type 1

5.9.1 Eye Patterns (continued)

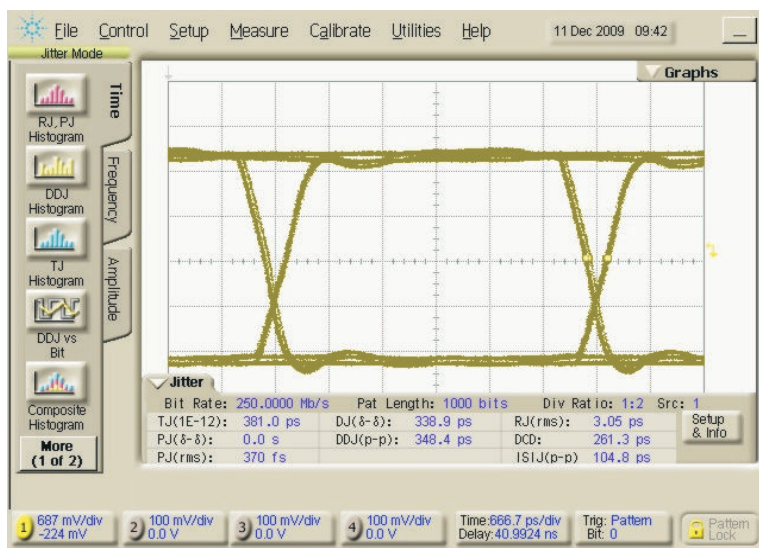


图 5-12. Output ($V_{CC} = 3.3V$, $V_{ID} = 800mV$) 250Mbps $2^{15} - 1$ PRBS, Receiver Type 2

6 Parameter Measurement Information

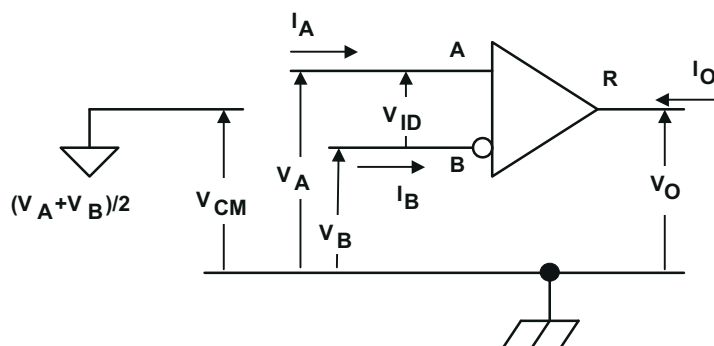


图 6-1. Receiver Voltage and Current Definitions

表 6-1. Type-1 Receiver Input Threshold Test Voltages

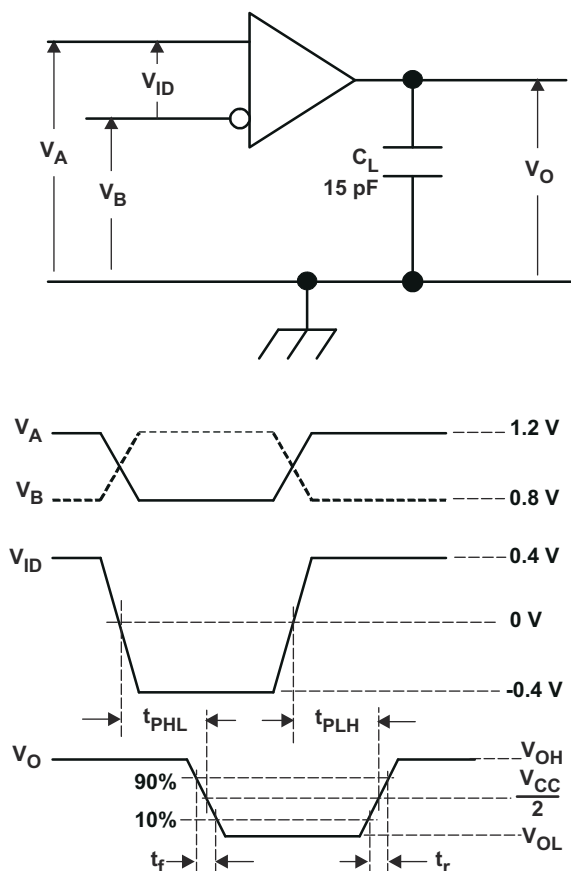
APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾
V_{IA}	V_{IB}	V_{ID}	V_{IC}	
2.400	0.000	2.400	1.200	H
0.000	2.400	- 2.400	1.200	L
3.400	3.365	0.035	3.3825	H
3.365	3.400	- 0.035	3.3825	L
- 0.965	- 1	0.035	- 0.9825	H
- 1	- 0.965	- 0.035	- 0.9825	L

(1) H= high level, L = low level, output state assumes receiver is enabled ($\overline{RE} = L$)

表 6-2. Type-2 Receiver Input Threshold Test Voltages

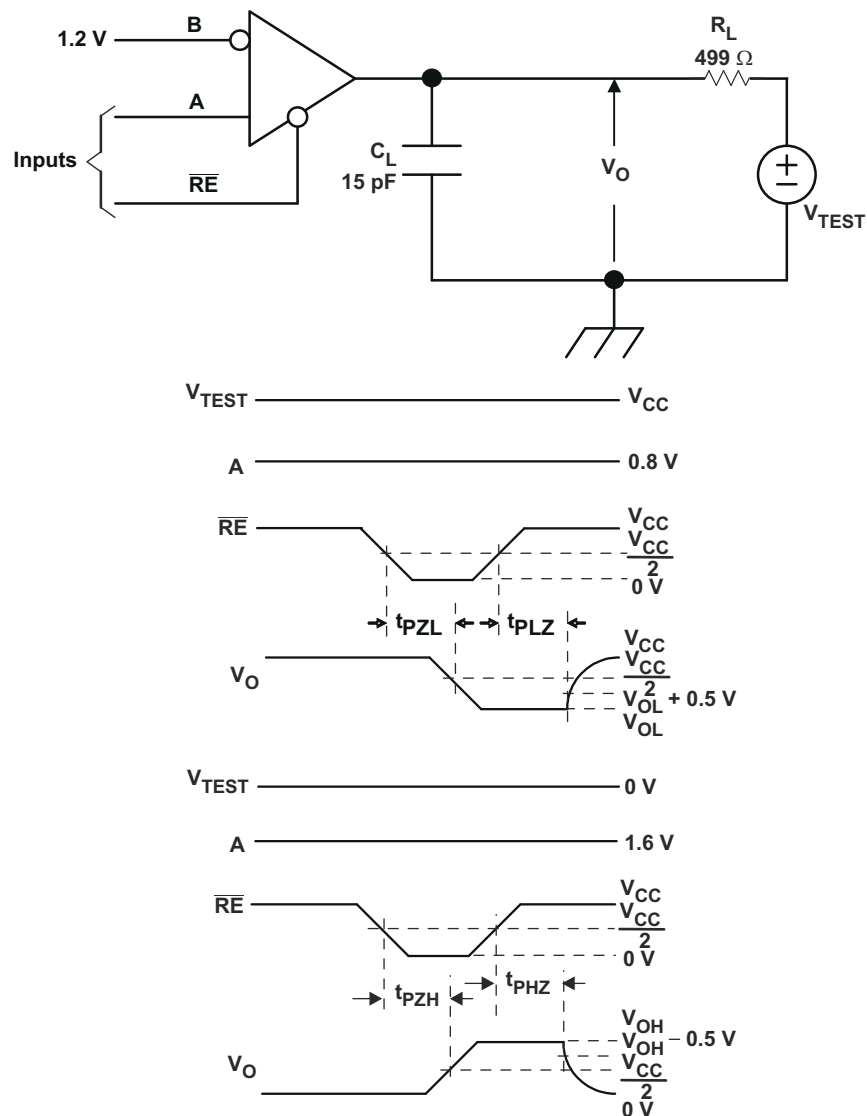
APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾
V_{IA}	V_{IB}	V_{ID}	V_{IC}	
2.400	0.000	2.400	1.200	H
0.000	2.400	- 2.400	1.200	L
3.400	3.265	0.135	3.3325	H
3.4000	3.335	0.05065	3.3675	L
- 0.865	- 1	0.135	- 0.9325	H
-0.935	- 1	0.065	- 0.9675	L

(1) H= high level, L = low level, output state assumes receiver is enabled ($\overline{RE} = L$)



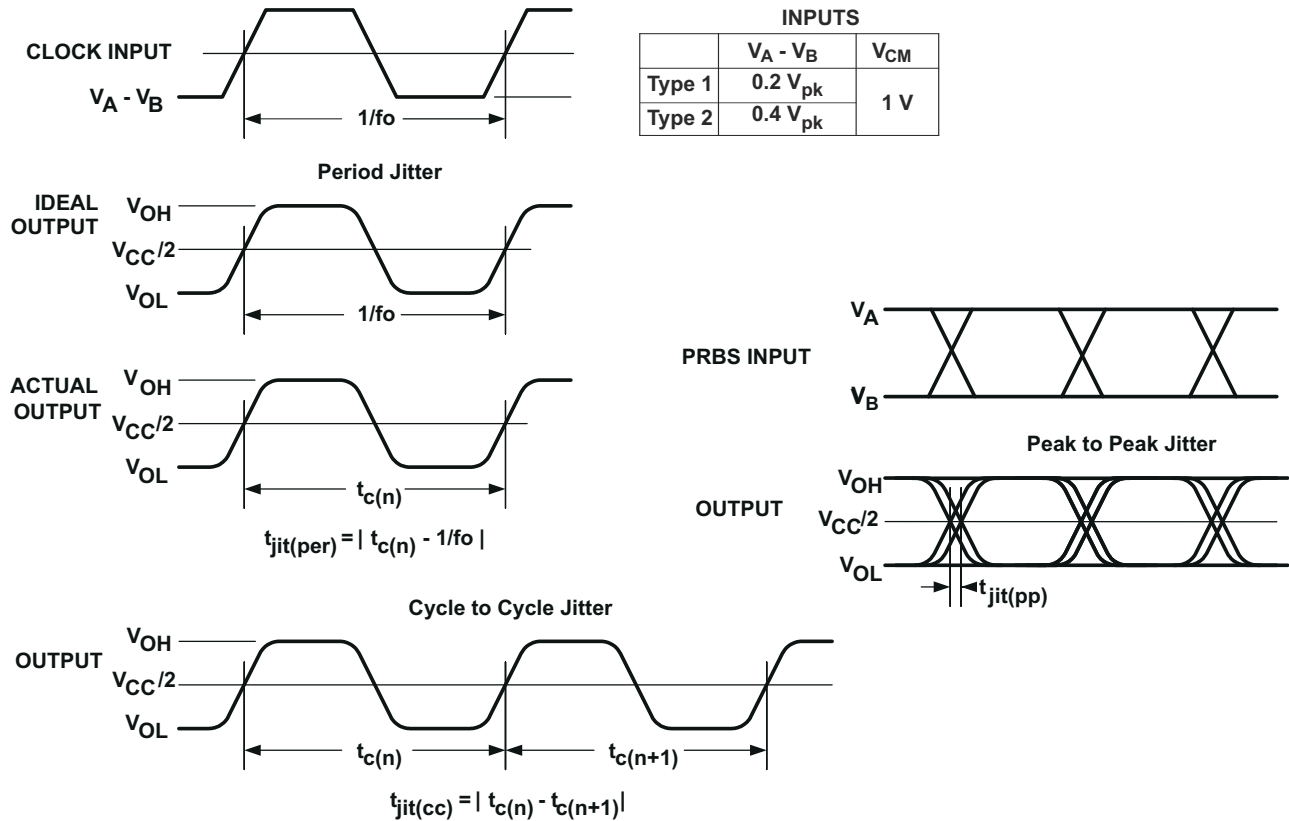
- All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, Frequency = 1 MHz, duty cycle = $50 \pm 5\%$. C_L is a combination of a 20%-tolerance, low-loss ceramic, surface-mount capacitor and fixture capacitance within 2 cm of the D.U.T.
- The measurement is made on test equipment with a - 3dB bandwidth of at least 1 GHz.

图 6-2. Receiver Timing Test Circuit and Waveforms



- All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1\text{ns}$, frequency = 1MHz, duty cycle = $50 \pm 5\%$.
- R_L is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.
- C_L is the instrumentation and fixture capacitance within 2 cm of the D.U.T. and $\pm 20\%$. The measurement is made on test equipment with a - 3dB bandwidth of at least 1GHz.

图 6-3. Receiver Enable/Disable Time Test Circuit and Waveforms



- All input pulses are supplied by the Agilent 81250 Parallel BERT Stimulus System with plug-in E4832A.
- The cycle-to-cycle jitter measurement is made on a TEK TDS6604 running TDSJIT3 application software.
- All other jitter measurements are made with an Agilent Infiniium DCA-J 86100C Digital Communications Analyzer.
- Period jitter and cycle-to-cycle jitter are measured using a 125MHz $50 \pm 1\%$ duty cycle clock input. Measured over 75K samples.
- Deterministic jitter and random jitter are measured using a 250Mbps $2^{15} - 1$ PRBS input. Measured over $BER = 10^{-12}$

图 6-4. Receiver Jitter Measurement Waveforms

7 Device Functional Modes

表 7-1. Device Function Table

INPUTS ⁽¹⁾				RECEIVER TYPE	OUTPUT ⁽¹⁾
$V_{ID} = V_A - V_B$	PDN	FSEN	RE		R
$V_{ID} > 35\text{mV}$	H	L	L	Type 1	H
$-35\text{mV} \leq V_{ID} \leq 35\text{mV}$	H	L	L	Type 1	?
$V_{ID} < -35\text{mV}$	H	L	L	Type 1	L
$V_{ID} > 135\text{mV}$	H	H	L	Type 2	H
$65\text{mV} \leq V_{ID} \leq 135\text{mV}$	H	H	L	Type 2	?
$V_{ID} < 65\text{mV}$	H	H	L	Type 2	L
Open Circuit	H	L	L	Type 1	?
Open Circuit	H	H	L	Type 2	L
X	H	X	H	X	Z
X	H	X	OPEN	X	Z
X	L	X	X	X	Z

(1) H=high level, L=low level, Z=high impedance, X=Don't care, ?=indeterminate

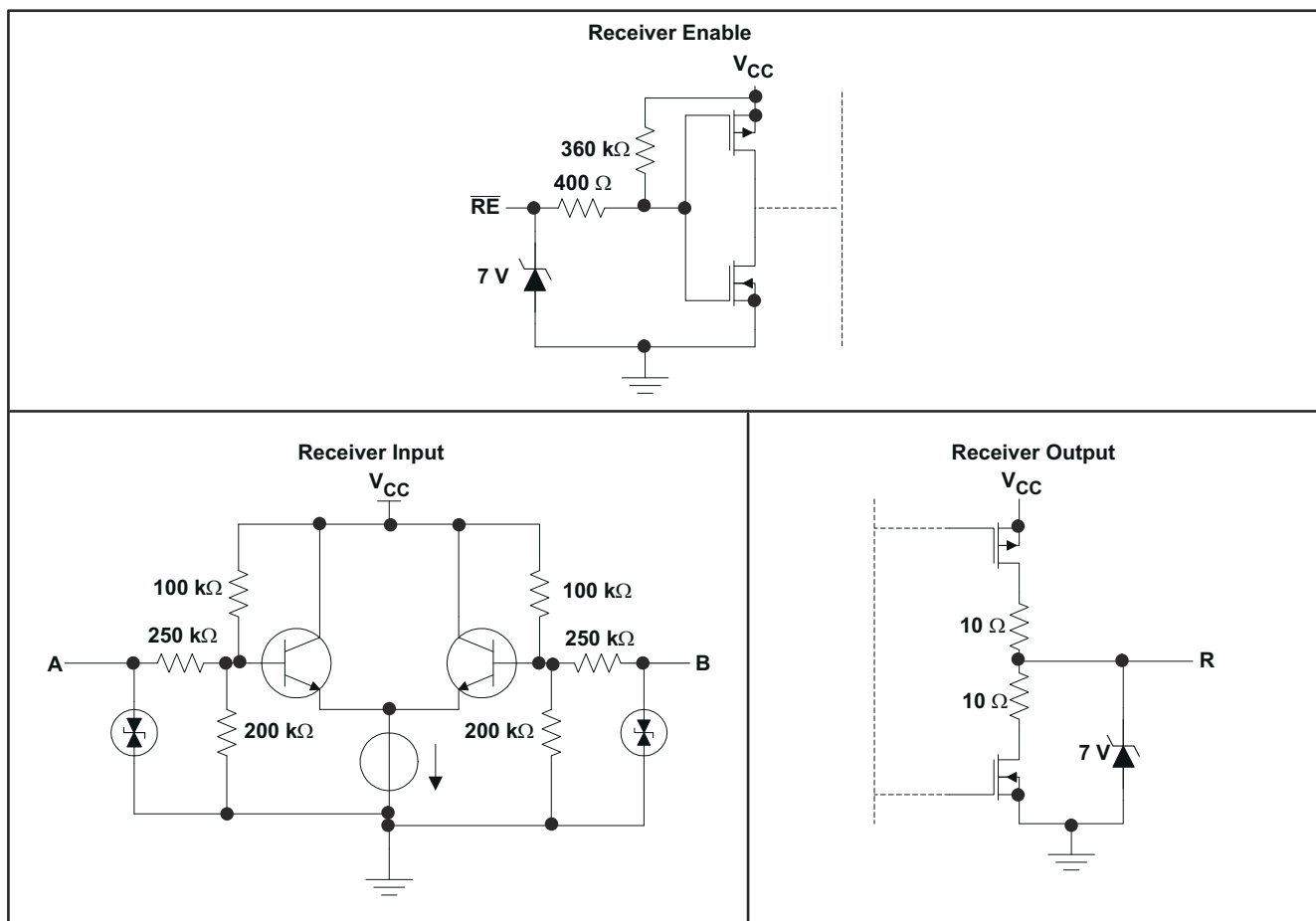


图 7-1. Equivalent Input and Output Schematic Diagrams

8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [通知](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

8.2 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

8.3 Trademarks

PowerPAD™ and TI E2E™ are trademarks of Texas Instruments.

所有商标均为其各自所有者的财产。

8.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

8.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision * (December 2009) to Revision A (March 2024)	Page
• 更改了整个文档中的表格、图和交叉参考的编号格式.....	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN65MLVD048RGZR	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048
SN65MLVD048RGZR.B	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048
SN65MLVD048RGZT	Active	Production	VQFN (RGZ) 48	250 SMALL T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048
SN65MLVD048RGZT.B	Active	Production	VQFN (RGZ) 48	250 SMALL T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048
SN65MLVD048RGZTG4	Active	Production	VQFN (RGZ) 48	250 SMALL T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048
SN65MLVD048RGZTG4.B	Active	Production	VQFN (RGZ) 48	250 SMALL T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65MLVD048RGZR	VQFN	RGZ	48	2500	330.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2
SN65MLVD048RGZT	VQFN	RGZ	48	250	180.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2
SN65MLVD048RGZTG4	VQFN	RGZ	48	250	180.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65MLVD048RGZR	VQFN	RGZ	48	2500	353.0	353.0	32.0
SN65MLVD048RGZT	VQFN	RGZ	48	250	213.0	191.0	35.0
SN65MLVD048RGZTG4	VQFN	RGZ	48	250	213.0	191.0	35.0

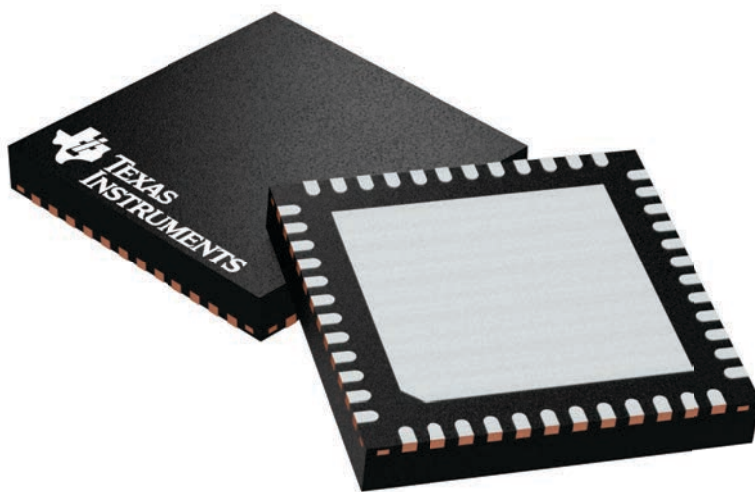
GENERIC PACKAGE VIEW

RGZ 48

VQFN - 1 mm max height

7 x 7, 0.5 mm pitch

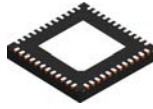
PLASTIC QUADFLAT PACK- NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4224671/A

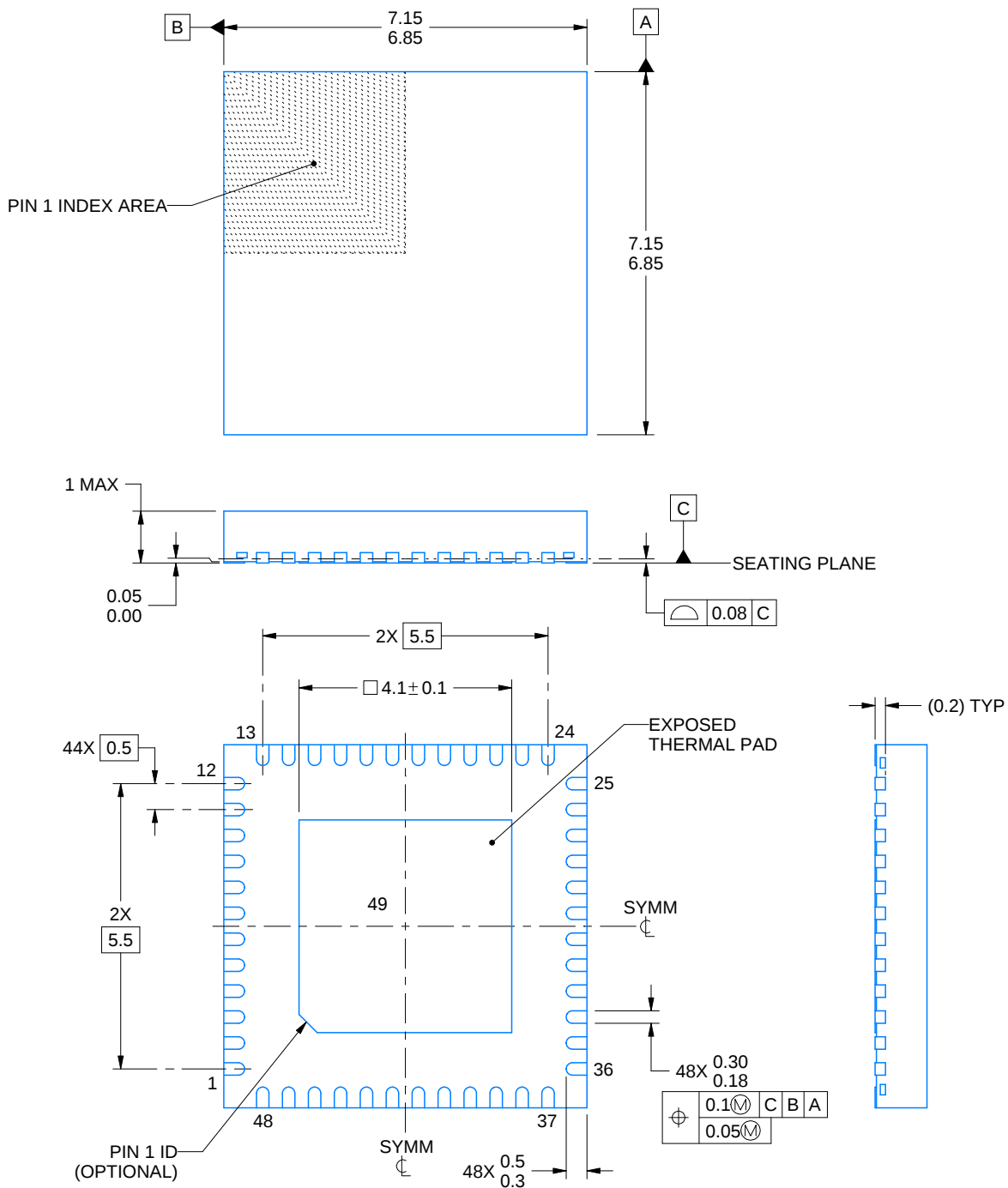
RGZ0048B



PACKAGE OUTLINE

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4218795/B 02/2017

NOTES:

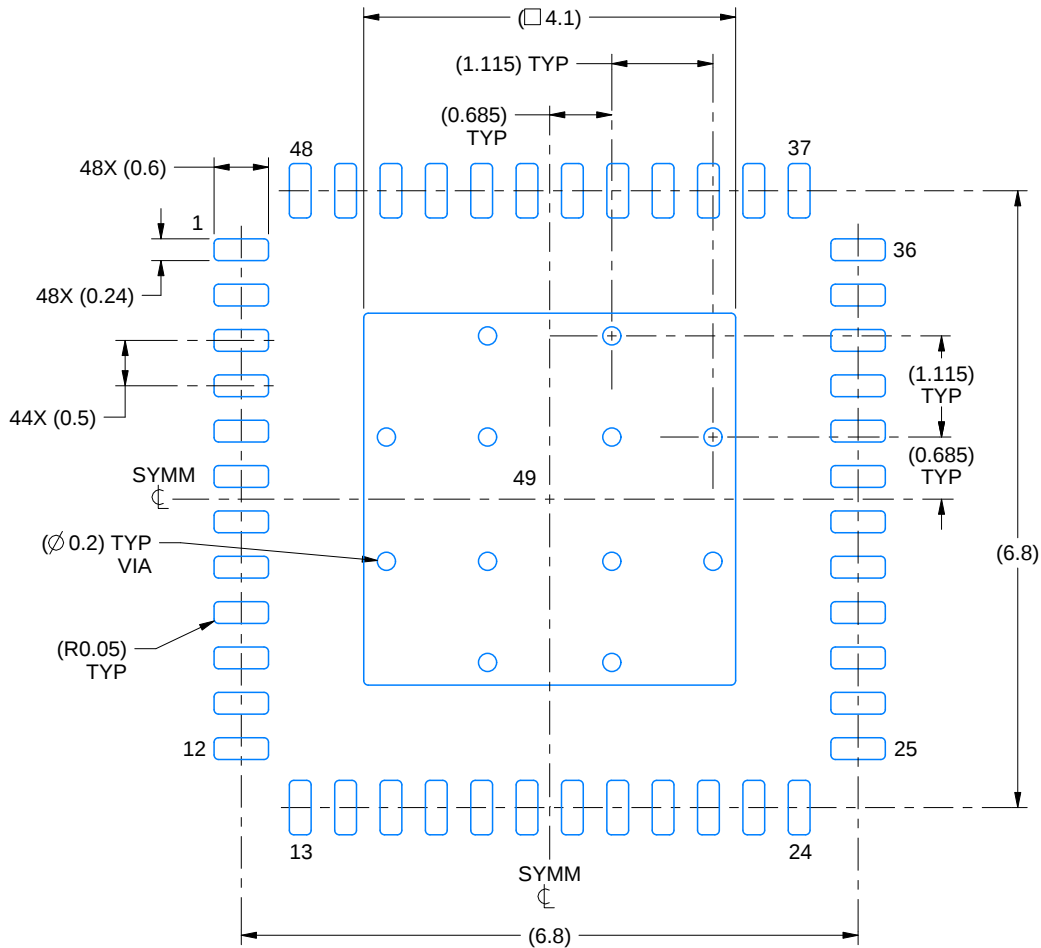
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

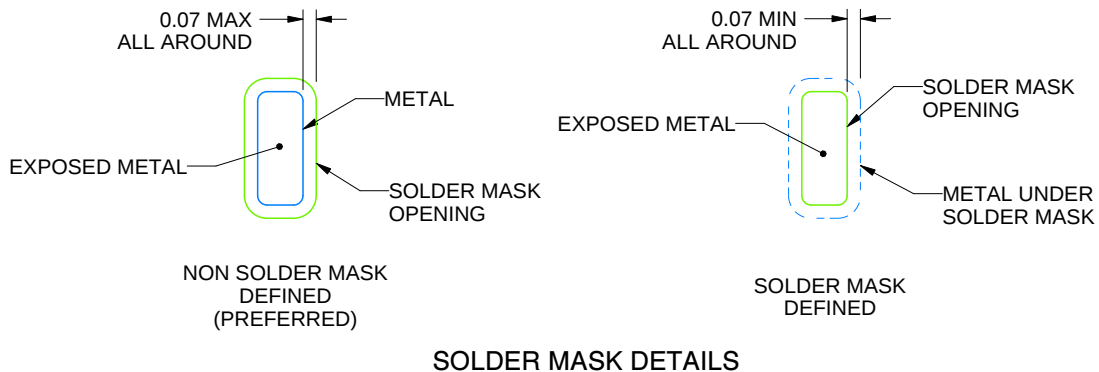
RGZ0048B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:12X



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NOTES: (continued)

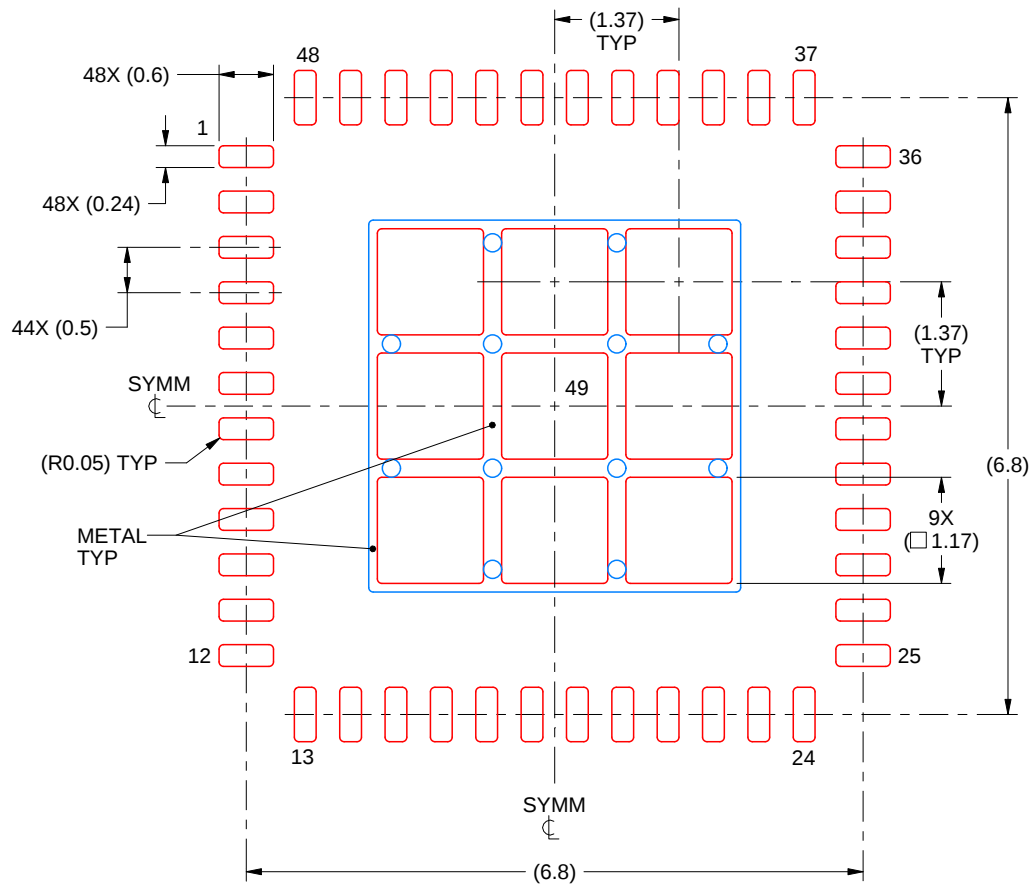
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGZ0048B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 49
73% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:12X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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